

650V 20A N-Channel SIC Power MOSFE

Features

- High blocking voltage with low on-resistance High
- speed switching with low capacitance Wide Bandgap
- SiC MOSFET Technology Halogen free, RoHs
- compliant

Mechanical Data

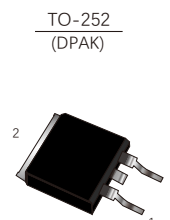
- Case:TO-252 Package

Application

- Switch Mode Power Supplies High
- Voltage DC/DC Converters Battery
- Chargers
- Pulsed Power Applications Motor
- Drives

Product Summary			
V _{DS}	R _{DS(on)} (mΩ)Typ	I _D (A)	Q _g (Typ)
650V	180@ 15V 8.5A	20	28nc

Marking:SC180N65M / JF SC180N65M



Block Diagram

Pin Definition:

1. Gate
2. Drain
3. Source

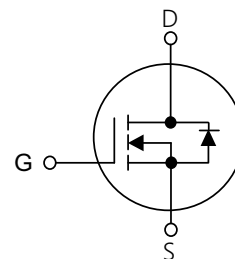


Table1 Absolute Maximum Ratings (T_C=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	650	V
Gate-Source Voltage(Max)	V _{GS(max)}	-10/+22	V
Recommend Gate-Source Voltage	V _{GSop}	0/+18	V
Continuous Drain Current	I _D	T _C =25°C	20
		T _C =100°C	18
Pulsed Drain Current (Note 1)	I _{DM}	40	A
Power Dissipation	P _D	52	W
Operating Junction and Storage Temperature	T _J /T _{STG}	-55 ~ +175	°C

Table 2. Thermal Characteristics

Parameter	Symbol	SC180N65M	Unit
Thermal resistance Junction to Case	R _{θjc}	2.88	°C/W

Table 3. Electrical Characteristics (T=25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =500μA	650	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V	-	-	10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =18V, V _{DS} =0V		250	nA
	Reverse		V _{GS} =-4V, V _{DS} =0V		-10	-250
On Characteristics						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =3.5mA	2.7	-	4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =15V, I _D =8.5A, T _J =25°C	-	180	240	mΩ
		V _{GS} =15V, I _D =8.5A, T _J =175°C	-	160	-	
		V _{GS} =18V, I _D =8.5A, T _J =25°C	-	120	-	
		V _{GS} =18V, I _D =8.5A, T _J =175°C	-	130	-	
Gate Resisitance	R _G	f=1MHz	-	6.5	-	Ω
Dynamic Characteristics						
Input Capacitance	C _{ISS}	V _{DS} =500V, V _{GS} =0V, f=1MHz	-	491	-	pF
Output Capacitance	C _{OSS}		-	39	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	4.2	-	pF
Turn-On Delay Time	td(on)	V _{DS} =500V, I _D =8.5A, V _{GS} =0/15V, R _G =10Ω, T _J =25°C	-	16	-	ns
Turn-On Rise Time	tr		-	55	-	ns
Turn-Off Delay Time	td(off)		-	34	-	ns
Turn-Off Fall Time	tf		-	71	-	ns
Total Gate Charge	Q _G	V _{DD} =500V, I _D =8.5A, V _{GS} =0/15V	-	28	-	nC
Gate-Source Charge	Q _{GS}		-	8.3	-	nC
Gate-Drain Charge	Q _{GD}		-	13.8	-	nC
Drain-Source Diode Characteristics and Maximum Ratings(Note 2)						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =5A	-	3.4	-	V
Continuous Diode Forward Current	I _S		-	20	-	A
Reverse Recovery Time	t _{rr}	V _R =500V, V _{GS} =0V, I _{SD} =8.5A, di/dt=530A/us	-	17.6	-	ns
Recovered charge	Q _{rr}		-	43	-	nC
Peak reverse recovery current	I _{rrm}		-	4.2	-	A

Notes: 1 RepetitivRating Blse width limited by maximum junction temperature

2 Pulse Test: Pulse width ≤300μS, Duty cycle ≤2%

Typical Characteristics Diagrams

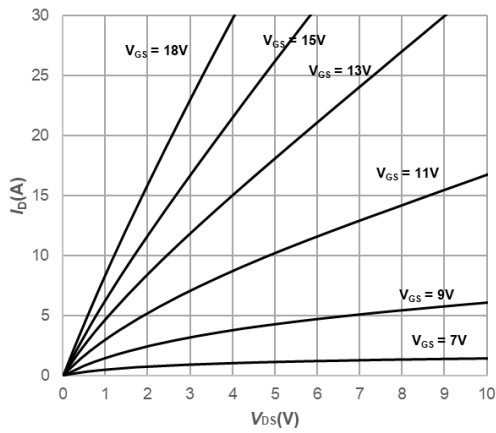


Fig1. Output Characteristics $T=25^{\circ}\text{C}$

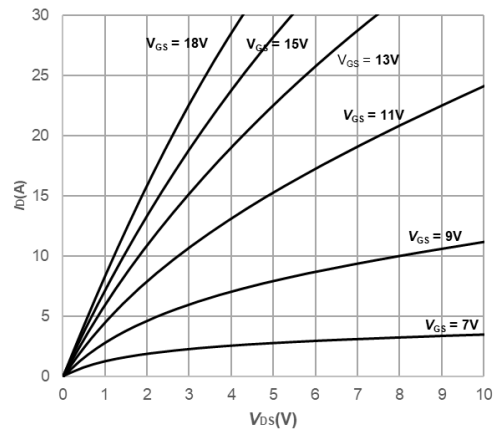


Fig2. Output Characteristics $T=175^{\circ}\text{C}$

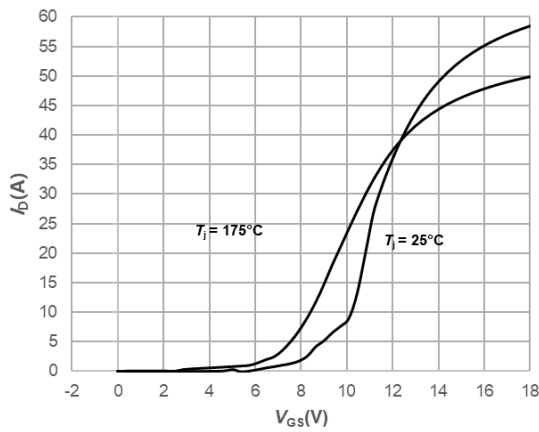


Fig3. Typical Transfer Characteristics

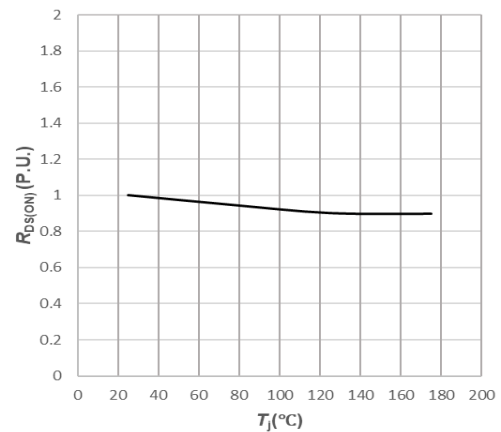


Fig4. Normalized On-Resistance vs. Temperature

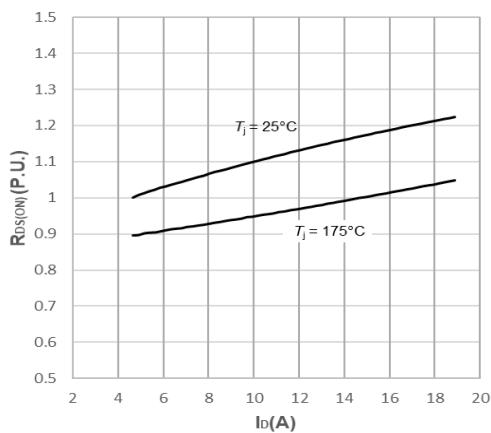


Fig5. Normalized On-Resistance vs. Drain Current For Various Temperatures

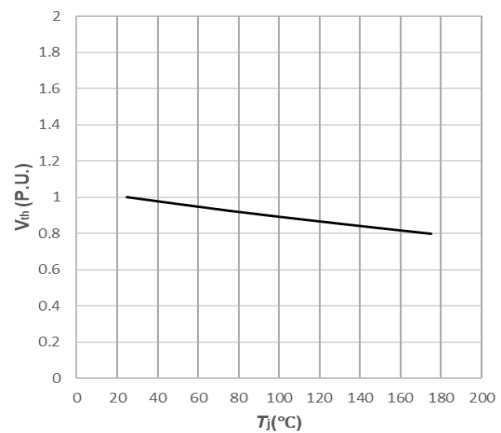


Fig6. Normalized Threshold Voltage vs. Temperature

Typical Characteristics Diagrams

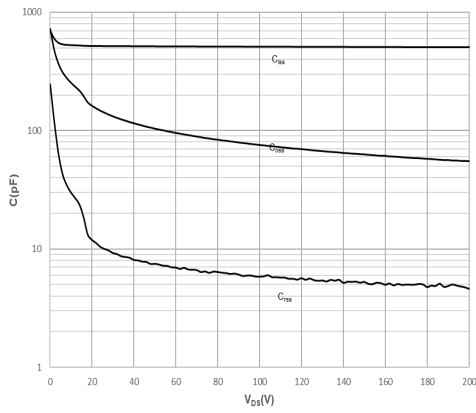


Fig7. Capacitances vs. Drain-Source Voltage (0-200V)

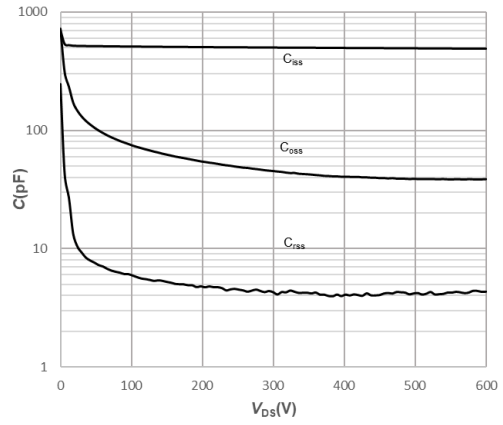


Fig8. Capacitances vs. Drain-Source Voltage (0-600V)

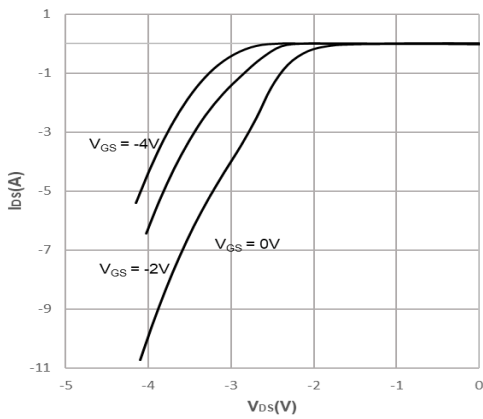
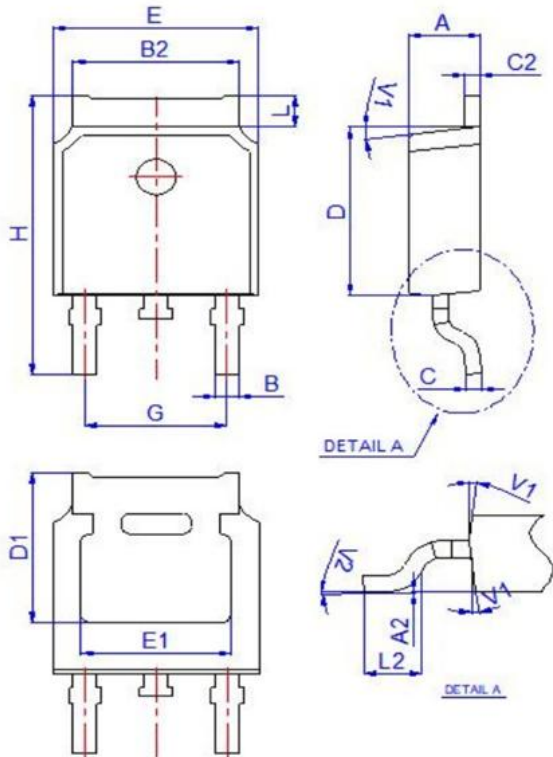


Fig9. Body Diode Characteristics

Dimensions

TO-252 package



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°